SGM8263-1/SGM8263-2 Ultra Low Offset Voltage, High Linearity, Low Noise Operational Amplifiers

GENERAL DESCRIPTION

The SGM8263-1 (single) and SGM8263-2 (dual) bipolar-input operational amplifiers achieve very low noise density with a low distortion of 0.0001% at 1kHz. The SGM8263-1/2 offer rail-to-rail output swing to within 190mV of supply rails with a $2k\Omega$ load, which increases headroom and maximizes dynamic range. The devices also have a high output drive capability of ±55mA.

SGM8263-1/2 have ultra low offset voltage and ultra low offset voltage drift over temperature. The maximum offset voltage is 8.5μ V. SGM8263-1/2 are very suitable for amplifying low noise and low amplitude signal.

The devices operate over a wide supply range of 4V to 36V or $\pm 2V$ to $\pm 18V$, on only 2.5mA of supply current per amplifier. The SGM8263-1/2 operational amplifiers are unity-gain stable and provide excellent dynamic behavior over a wide range of load conditions.

The SGM8263-1 is available in Green SOT-23-5 and SOIC-8 packages. The SGM8263-2 is available in a Green SOIC-8 package. They are specified from -40°C to +85°C temperature range.

FEATURES

- Ultra Low Offset Voltage: 8.5µV (MAX)
- Ultra Low Input Offset Voltage Drift: 10nV/°C
- Low Noise: 4.5nV/ \sqrt{Hz} at 1kHz
- Low Distortion: 0.0001% at 1kHz
- High Slew Rate: 10V/µs
- Gain-Bandwidth Product: 10MHz (G = +1)
- High Open-Loop Gain: 145dB
- Unity-Gain Stable
- Low Quiescent Current: 2.5mA/Amplifier
- Rail-to-Rail Output
- Support Single or Dual Power Supplies: 4V to 36V or ±2V to ±18V
- -40°C to +85°C Operating Temperature Range
- Small Packaging: SGM8263-1 Available in Green SOT-23-5 and SOIC-8 Packages SGM8263-2 Available in a Green SOIC-8 Package

APPLICATIONS

Temperature Measurements Pressure Sensors Precision Current Sensing Electronic Scales Strain Gauge Amplifiers Medical Instrumentation Thermocouple Amplifiers Handheld Test Equipment

PACKAGE/ORDERING INFORMATION

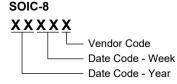
MODEL	PACKAGE DESCRIPTION			PACKAGE MARKING	PACKING OPTION
SGM8263-1	SOT-23-5	-40°C to +85°C	SGM8263-1YN5G/TR	GJ8XX	Tape and Reel, 3000
3GINI0203-1	SOIC-8	-40°C to +85°C	SGM8263-1YS8G/TR	SGM 82631YS8 XXXXX	Tape and Reel, 4000
SGM8263-2	SOIC-8	-40°C to +85°C	SGM8263-2YS8G/TR	SGM 82632YS8 XXXXX	Tape and Reel, 4000

MARKING INFORMATION

NOTE: XX = Date Code. XXXXX = Date Code and Vendor Code.



– Date Code - Month – Date Code - Year – Serial Number



Green (RoHS & HSF): SG Micro Corp defines "Green" to mean Pb-Free (RoHS compatible) and free of halogen substances. If you have additional comments or questions, please contact your SGMICRO representative directly.

ABSOLUTE MAXIMUM RATINGS

Supply Voltage, +V _S to -V _S	40V
Input Voltage Range (-Vs) - 0.3	√ to (+V _S) + 0.3V
Input Current (All pins except power supply	pins)±10mA
Output Short-Circuit Current	±80mA
Junction Temperature	+150°C
Storage Temperature Range	65°C to +150°C
Lead Temperature (Soldering, 10s)	+260°C
ESD Susceptibility	
HBM (SGM8263-1)	3000V
HBM (SGM8263-2)	5000V
MM (SGM8263-1)	200V
MM (SGM8263-2)	300V
CDM	1000V

RECOMMENDED OPERATING CONDITIONS

Operating Temperature Range-40°C to +85°C

OVERSTRESS CAUTION

Stresses beyond those listed in Absolute Maximum Ratings may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect reliability. Functional operation of the device at any conditions beyond those indicated in the Recommended Operating Conditions section is not implied.

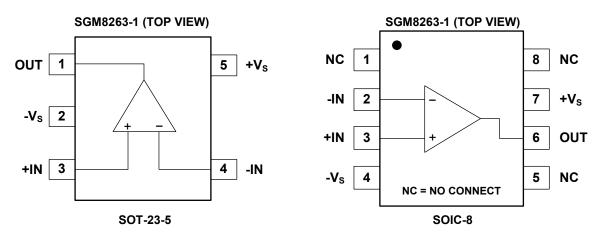
ESD SENSITIVITY CAUTION

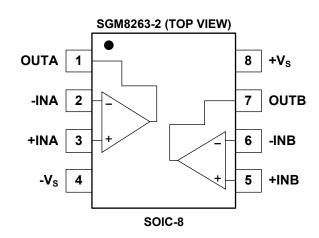
This integrated circuit can be damaged if ESD protections are not considered carefully. SGMICRO recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because even small parametric changes could cause the device not to meet the published specifications.

DISCLAIMER

SG Micro Corp reserves the right to make any change in circuit design, or specifications without prior notice.

PIN CONFIGURATIONS





ELECTRICAL CHARACTERISTICS

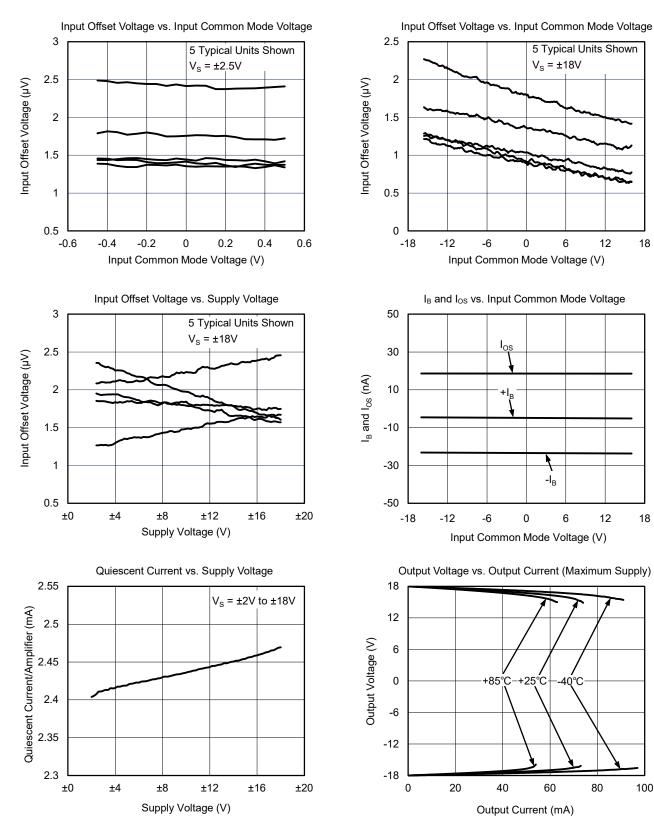
(At $T_A = +25^{\circ}$ C, $V_S = 4.5$ V to 36V or $V_S = \pm 2.25$ V to ± 18 V, $R_L = 2k\Omega$, $V_{CM} = V_{OUT} = V_S/2$, Full = -40°C to +85°C, unless otherwise noted.)

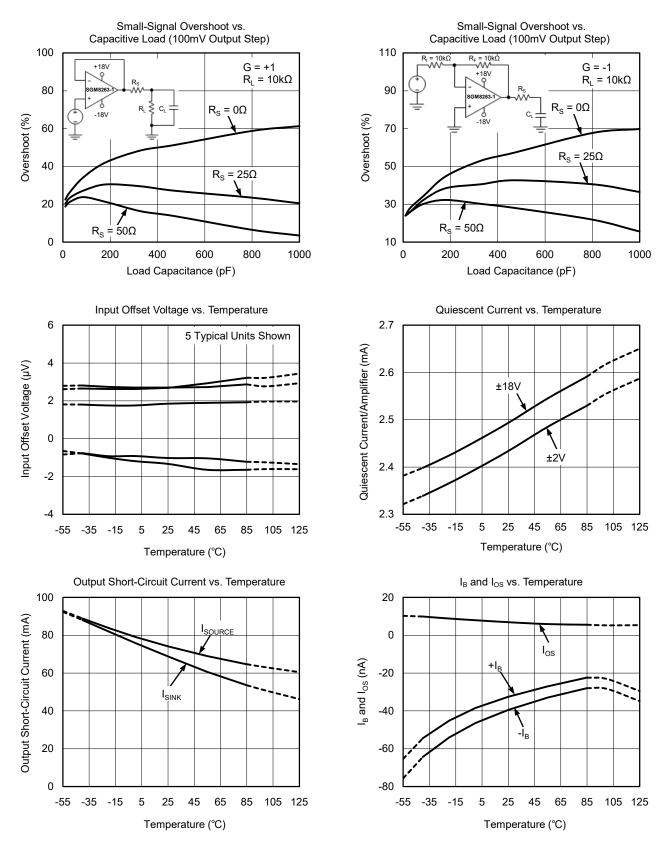
PARAMETER	SYMBOL	CONDITIONS	TEMP	MIN	TYP	MAX	UNITS
Input Characteristics							
					1.5	8.5	
Input Offset Voltage	Vos	$V_{\rm S} = \pm 15V$	Full			10	μV
Input Offset Voltage Drift	$\Delta V_{OS} / \Delta T$		Full		10		nV/°C
		V _{CM} = 0V			±60	±300	
Input Bias Current	IB					±350	nA
In much Offer and Country into		V _{CM} = 0V			±20	±190	
Input Offset Current	l _{os}					±210	nA
Input Common Mode Voltage Range	V _{CM}		Full	(-V _S) + 2		(+V _s) - 2	V
Common Mode Poinction Patio	CMRR	$(-V_{\rm S}) + 2V \le V_{\rm CM} \le (+V_{\rm S}) - 2V$	+25°C	107	135		dB
Common Mode Rejection Ratio	CIVIER	$(-v_S) + 2v \leq v_{CM} \leq (+v_S) - 2v$	Full	102			uБ
		$(-V_{\rm S}) + 0.2V \le V_{\rm OUT} \le (+V_{\rm S}) - 0.2V, R_{\rm I} = 10k\Omega$	+25°C	118	145		
Open Leen Veltage Cain	^	$(-v_S) + 0.2v \le v_{OUT} \le (+v_S) - 0.2v, R_L - 10R2$	Full	115			٩D
Open-Loop Voltage Gain	A _{OL}	$(-V_{\rm S}) + 0.6V \le V_{\rm OUT} \le (+V_{\rm S}) - 0.6V, R_{\rm I} = 2k\Omega$	+25°C	115	145		dB
		$(-v_{\rm S}) \neq 0.00 \leq v_{\rm OUT} \leq (+v_{\rm S}) - 0.00, R_{\rm L} - 2R\Omega$	Full	112			
Input Impedance							
Differential			+25°C		16k 10		Ω pF
Common Mode			+25°C		10 ⁹ 10		Ω pF
Output Characteristics							
			+25°C		40	75	
Output Voltage Swing from Bail		$R_{L} = 10k\Omega$				85	mV
Output Voltage Swing from Rail			+25°C		190	320	mv
		$R_{L} = 2k\Omega$	Full			360	
Output Short Circuit Current			+25°C	±36	±55		
Output Short-Circuit Current	I _{SC}		Full	±27			mA
Dynamic Performance							
Gain-Bandwidth Product	GBP	G = +1	+25°C		10		MHz
Phase Margin	φο	$V_{OUT} = 100mV_{P-P}, R_L = 2k\Omega, C_L = 10pF$	+25°C		50		٥
Slew Rate	SR	$G = -1, V_{OUT} = 2V_{P-P}$	+25°C		10		V/µs
Settling Time to 0.1%	ts	10V step, G = +1	+25°C		3		μs
Overload Recovery Time		$V_{IN} \times G > V_S$	+25°C		0.2		μs
Total Harmonic Distortion + Noise	THD+N	$G = +1$, $V_{OUT} = 1V_{RMS}$, $f = 1kHz$, $BW = 80kHz$	+25°C		0.0001		%
Noise Performance		I	1				
Input Voltage Noise		f = 0.1Hz to 10Hz	+25°C		100		nV_{P-P}
Input Voltage Noise Density	en	f = 1kHz	+25°C		4.5		nV/√Hz
Input Current Noise Density	in	f = 1kHz	+25°C		5		pA/√Hz
Power Supply	1	1	-	1		1	
Supply Voltage	Vs		Full	±2		±18	V
			+25°C		2.5	3.2	
Quiescent Current/Amplifier	Ι _Q	I _{OUT} = 0A	Full			3.4	mA
	D.C		+25°C		0.02	0.4	
Power Supply Rejection Ratio	PSRR	$V_{\rm S} = \pm 2V$ to $\pm 18V$				0.6	μV/V

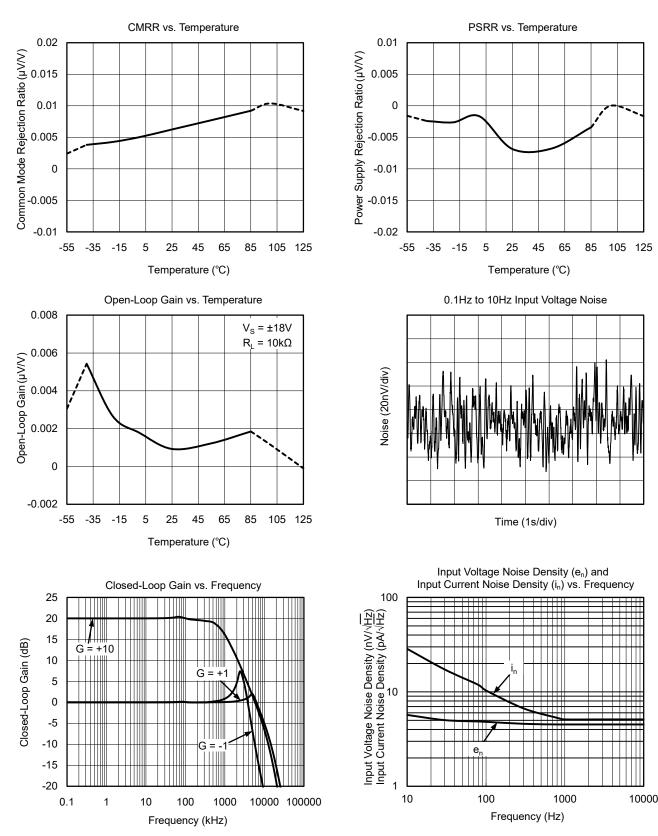
18

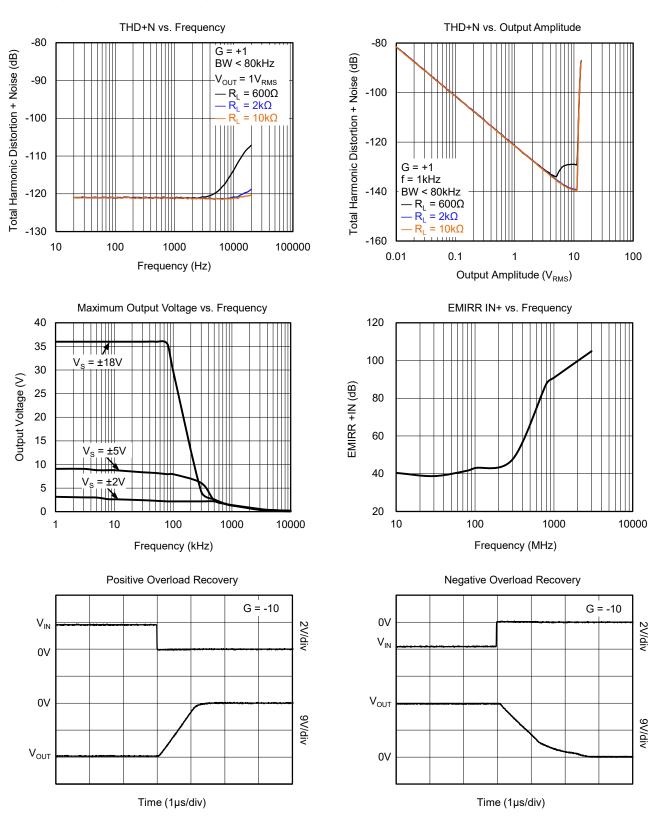
18

TYPICAL PERFORMANCE CHARACTERISTICS

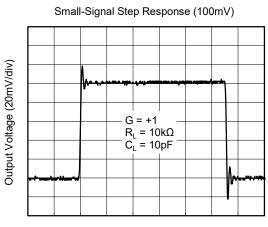




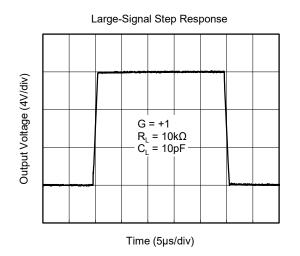


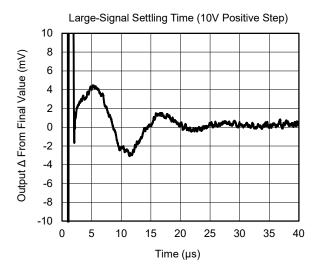


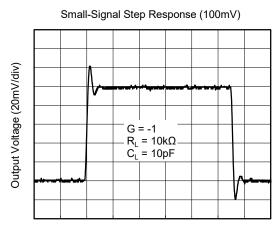
At $T_A = +25^{\circ}C$, $V_S = \pm 18V$ and $R_L = 10k\Omega$, unless otherwise noted.



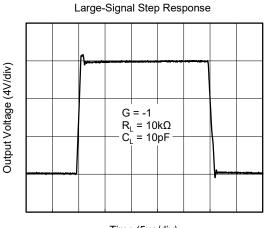
Time (500ns/div)



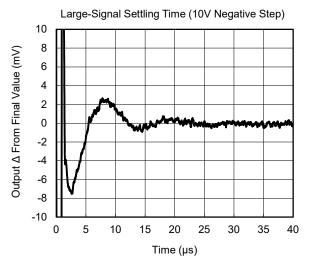


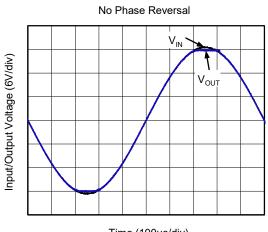


Time (500ns/div)

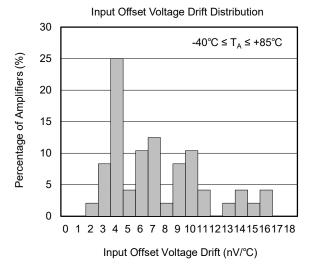


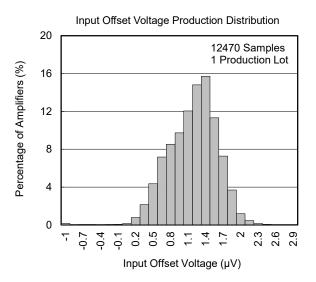












APPLICATION INFORMATION

The SGM8263-1/2 are unity-gain stable, high precision operational amplifiers with very low noise, very low offset voltage and very low offset voltage drift; the devices are also free from output phase reversal. Applications with noisy or high-impedance power supplies require decoupling capacitors close to the device power supply pins. In most cases, 0.1μ F capacitors are adequate.

Operating Voltage

The SGM8263-1/2 operational amplifiers operate from 4V to 36V or \pm 2V to \pm 18V supplies while maintaining excellent performance. However, some applications do not require equal positive and negative output voltage swing. With the SGM8263-1/2, power supply voltages do not need to be equal. For example, the positive supply could be set to 25V with the negative supply at -5V. In all cases, the input common mode voltage must be maintained within the specified range. In addition, key parameters are assured over the specified temperature range of T_A = -40°C to +85°C.

Input Protection

The input terminals of the SGM8263-1/2 are protected from excessive differential voltage with back-to-back diodes, as Figure 1 illustrates. In most circuit applications, the input protection circuitry has no consequence. However, in low-gain or G = +1 circuits, fast ramping input signals can forward bias these diodes because the output of the amplifier cannot respond rapidly enough to the input ramp. If the input signal is fast enough to create this forward bias condition, the input signal current must be limited to 10mA or less. If the input signal current is not inherently limited, an input series resistor (R_I) and/or a feedback resistor (R_F) can be used to limit the signal input current. This input series resistor degrades the low-noise performance of the SGM8263-1/2 and is examined in the following Noise Performance section. Figure 1 shows an example configuration when both current-limit input and feedback resistors are used.

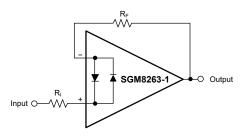


Figure 1. Input Current Limiting

Noise Performance

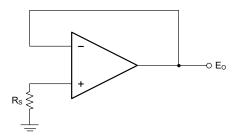
Equation 1 shows the total circuit noise for varying source impedances with the operational amplifier in a unity-gain configuration (Figure 2, no feedback resistor network, and therefore no additional noise contributions).

The SGM8263-1/2 (GBP = 10MHz, G = +1) are shown with total circuit noise calculated. The operational amplifier itself contributes both a voltage noise component and a current noise component. The voltage noise is commonly modeled as a time-varying component of the offset voltage. The current noise is modeled as the time-varying component of the input bias current and reacts with the source resistance to create a voltage component of noise. Therefore, the lowest noise operational amplifier for a given application depends on the source impedance. For low source impedance, current noise is negligible, and voltage noise generally dominates. The low voltage noise of the SGM8263-1/2 operational amplifiers makes them good choices for use in applications where the source impedance is less than $1k\Omega$.

The equation 1 shows the calculation of the total circuit noise, with these parameters:

- e_n = voltage noise
- i_n = current noise
- R_s = source impedance
- k = Boltzmann's constant = 1.38×10^{-23} J/K
- T = temperature in degrees Kelvin (K)

$$E_{o}^{2} = e_{n}^{2} + (i_{n}R_{s})^{2} + 4kTR_{s}$$
 (1)



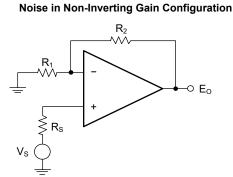
APPLICATION INFORMATION (continued)

Basic Noise Calculations

Design of low-noise operational amplifier circuits requires careful consideration of a variety of possible noise contributors: noise from the signal source, noise generated in the operational amplifier and noise from the feedback network resistors. The total noise of the circuit is the root-sum-square combination of all noise components.

The resistive portion of the source impedance produces thermal noise proportional to the square root of the resistance. The source impedance is usually fixed; consequently, select the operational amplifier and the feedback resistors to minimize the respective contributions to the total noise. Figure 3 illustrates both inverting and non-inverting operational amplifier circuit configurations with gain. In circuit configurations with gain, the feedback network resistors also contribute noise.

The current noise of the operational amplifier reacts with the feedback resistors to create additional noise components. The feedback resistor values can generally be chosen to make these noise sources negligible. The equations for total noise are shown for both configurations.

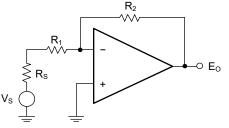


Noise at the output:

$$E_0^2 = \left[1 + \frac{R_2}{R_1}\right]^2 e_n^2 + e_1^2 + e_2^2 + (i_r R_2)^2 + e_s^2 + (i_r R_s)^2 \left[1 + \frac{R_2}{R_1}\right]^2$$

Where $e_s = \sqrt{4kTR_s} \times \left[1 + \frac{R_2}{R_1}\right]$ = thermal noise of R_s
 $e_1 = \sqrt{4kTR_1} \times \left[\frac{R_2}{R_1}\right]$ = thermal noise of R_1
 $e_2 = \sqrt{4kTR_2}$ = thermal noise of R_2

Noise in Inverting Gain Configuration



Noise at the output:

$$E_{o}^{2} = \left[1 + \frac{R_{2}}{R_{1} + R_{s}}\right]^{2} e_{n}^{2} + e_{1}^{2} + e_{2}^{2} + (i_{n}R_{2})^{2} + e_{s}^{2}$$
Where $e_{s} = \sqrt{4kTR_{s}} \times \left[\frac{R_{2}}{R_{1} + R_{s}}\right]$ = thermal noise of R_{s}

$$e_{1} = \sqrt{4kTR_{1}} \times \left[\frac{R_{2}}{R_{1} + R_{s}}\right]$$
 = thermal noise of R_{1}

$$e_{2} = \sqrt{4kTR_{2}}$$
 = thermal noise of R_{2}

NOTE: For the SGM8263-1/2 operational amplifiers at 1kHz, e_n = 4.5nV/ $\sqrt{_{Hz}}~$ and i_n = 5pA/ $\sqrt{_{Hz}}$.

Figure 3. Noise Calculation in Gain Configurations

APPLICATION INFORMATION (continued)

Capacitive Loads

The dynamic characteristics of the SGM8263-1/2 have been optimized for commonly encountered gains, loads and operating conditions. The combination of low closed-loop gain and high capacitive loads decreases the phase margin of the amplifier and can lead to gain peaking or oscillations. As a result, heavier capacitive loads must be isolated from the output. The simplest way to achieve this isolation is to add a small resistor (R_s equal to 50 Ω , for example) in series with the output.

Power Dissipation

SGM8263-1/2 operational amplifiers are capable of driving $2k\Omega$ loads with a power supply voltage up to ±18V. Internal power dissipation increases when operating at high supply voltages. Copper leadframe construction used in the SGM8263-1/2 operational amplifiers improves heat dissipation compared to conventional materials. Circuit board layout can also

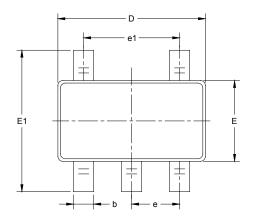
help minimize junction temperature rise. Wide copper traces help dissipate the heat by acting as an additional heat sink. Temperature rise can be further minimized by soldering the devices to the circuit board rather than using a socket.

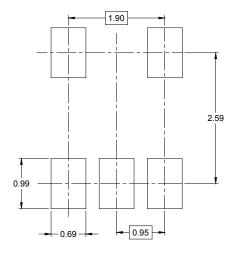
Electrical Overstress

Designers often ask questions about the capability of an operational amplifier to withstand electrical overstress. These questions tend to focus on the device inputs, but may involve the supply voltage pins or even the output pin. Each of these different pin functions has electrical stress limits determined by the voltage breakdown characteristics of the particular semiconductor fabrication process and specific circuits connected to the pin. Additionally, internal electrostatic discharge (ESD) protection is built into these circuits to protect them from accidental ESD events both before and during product assembly.

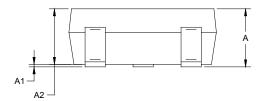
PACKAGE OUTLINE DIMENSIONS

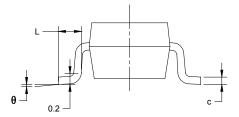
SOT-23-5





RECOMMENDED LAND PATTERN (Unit: mm)

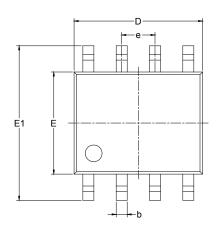


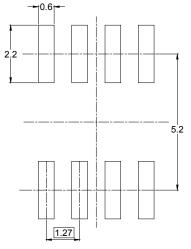


Symbol	-	nsions meters	Dimensions In Inches		
	MIN	MAX	MIN	MAX	
А	1.050	1.250	0.041	0.049	
A1	0.000	0.100	0.000	0.004	
A2	1.050	1.150	0.041	0.045	
b	0.300	0.500	0.012	0.020	
С	0.100	0.200	0.004	0.008	
D	2.820	3.020	0.111	0.119	
E	1.500	1.700	0.059	0.067	
E1	2.650	2.950	0.104	0.116	
e	0.950 BSC		0.037 BSC		
e1	1.900 BSC		0.075	BSC	
L	0.300	0.600	0.012	0.024	
θ	0°	8°	0°	8°	

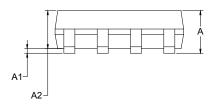
PACKAGE OUTLINE DIMENSIONS

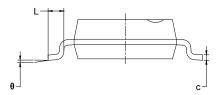
SOIC-8





RECOMMENDED LAND PATTERN (Unit: mm)

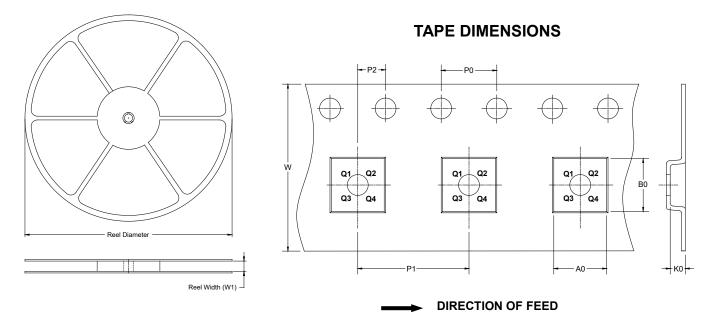




Symbol		nsions meters	Dimensions In Inches			
	MIN	MAX	MIN	MAX		
A	1.350	1.750	0.053	0.069		
A1	0.100	0.250	0.004	0.010		
A2	1.350	1.550	0.053	0.061		
b	0.330	0.510	0.013	0.020		
С	0.170	0.250	0.006	0.010		
D	4.700	5.100	0.185	0.200		
E	3.800	4.000	0.150	0.157		
E1	5.800	6.200	0.228	0.244		
е	1.27 BSC		0.050	BSC		
L	0.400	1.270	0.016	0.050		
θ	0°	8°	0°	8°		

TAPE AND REEL INFORMATION

REEL DIMENSIONS



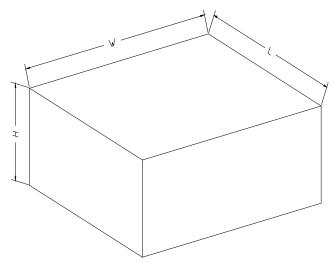
NOTE: The picture is only for reference. Please make the object as the standard.

KEY PARAMETER LIST OF TAPE AND REEL

Package Type	Reel Diameter	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P0 (mm)	P1 (mm)	P2 (mm)	W (mm)	Pin1 Quadrant
SOT-23-5	7″	9.5	3.20	3.20	1.40	4.0	4.0	2.0	8.0	Q3
SOIC-8	13″	12.4	6.40	5.40	2.10	4.0	8.0	2.0	12.0	Q1

DD0002

CARTON BOX DIMENSIONS



NOTE: The picture is only for reference. Please make the object as the standard.

Reel Type	Length (mm)	Width (mm)	Height (mm)	Pizza/Carton
7" (Option)	368	227	224	8
7"	442	410	224	18
13″	386	280	370	5

KEY PARAMETER LIST OF CARTON BOX